NSN 5962-01-375-9297

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View Online at https://aerobasegroup.com/nsn/5962-01-375-9297 **Body Length:** 1.060 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 2.0 watts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **End Application:** 6625-01-323-3125 test set, computer **Features Provided:** Bipolar and programmed and high impedance and w/enable and w/disable and electrostatic sensitive and bidirectional **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 16 input **Case Outline Source And Designator:**

D-8 mil-m-38510

Current Rating Per Characteristic:

180.00 milliamperes reverse current, dc absolute

Terminal Surface Treatment:

Solder

Product Name:

And-or invert gate array

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 12.0 volts power source

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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